CY62157E MoBL®

8-Mbit (512K x 16) Static RAM

Features

- Very high speed: 45 ns
  - Industrial: –40°C to +85°C
  - Automotive-E: –40°C to +125°C
- Wide voltage range: 4.5V–5.5V
- Ultra low standby power
  - Typical Standby current: 2 μA
  - Maximum Standby current: 8 μA (Industrial)
- Ultra low active power
  - Typical active current: 1.8 mA @ f = 1 MHz
- Ultra low standby power
- Easy memory expansion with $\overline{CE}_1$, CE_2 and $\overline{OE}$ features
- Automatic power down when deselected
- CMOS for optimum speed and power
- Available in Pb-free 44-pin TSOP II and 48-ball VFBGA package

Functional Description[1]

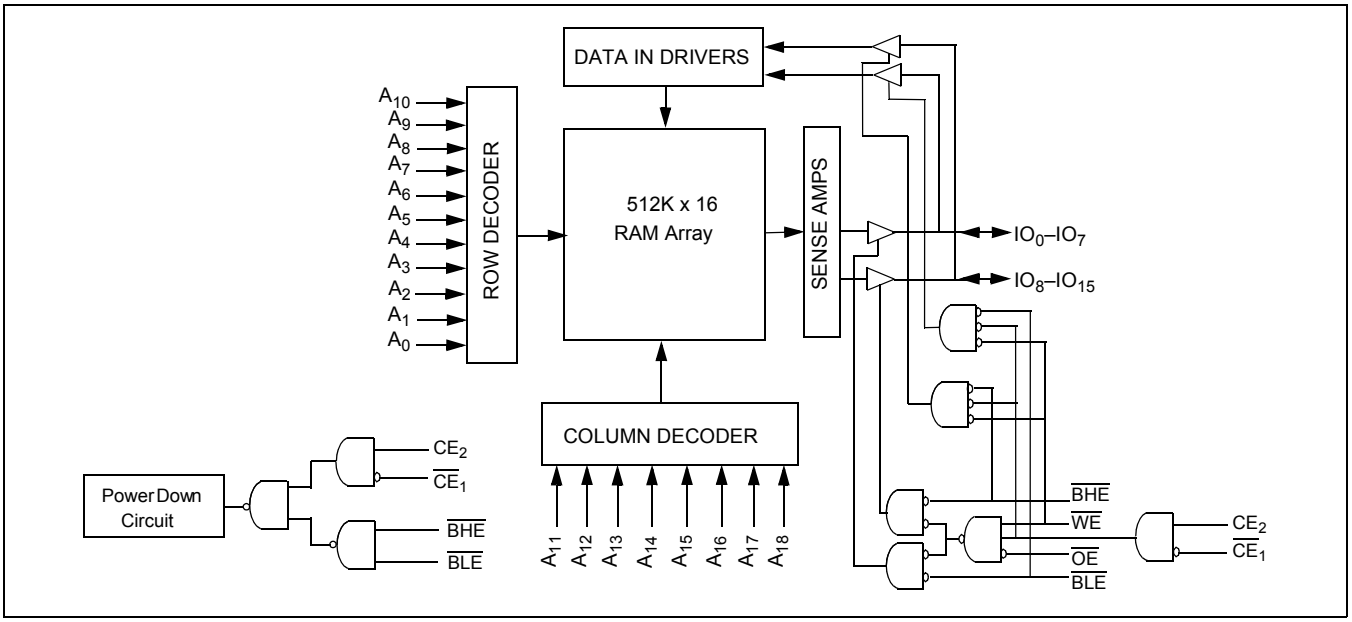
The CY62157E is a high performance CMOS static RAM organized as 512K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Place the device into standby mode when deselected ($\overline{CE}_1$ HIGH or CE_2 LOW or both $\overline{BHE}$ and $\overline{BLE}$ are HIGH). The input or output pins (IO_0 through IO_{15}) are placed in a high impedance state when:

- Deselected ($\overline{CE}_1$HIGH or CE_2 LOW)
- Outputs are disabled ($\overline{OE}$ HIGH)
- Both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH)
- Write operation is active ($\overline{CE}_1$ LOW, CE_2 HIGH and $\overline{WE}$ LOW)

To write to the device, take Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from IO pins (IO_0 through IO_7), is written into the location specified on the address pins (A_0 through A_{18}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from IO pins (IO_8 through IO_{15}) is written into the location specified on the address pins (A_0 through A_{18}).

To read from the device, take Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins appear on IO_0 to IO_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory appears on IO_8 to IO_{15}. See the "Truth Table" on page 9 for a complete description of read and write modes.

Logic Block Diagram



Notes
1. For best practice recommendations, please refer to the Cypress application note AN1064, SRAM System Guidelines.

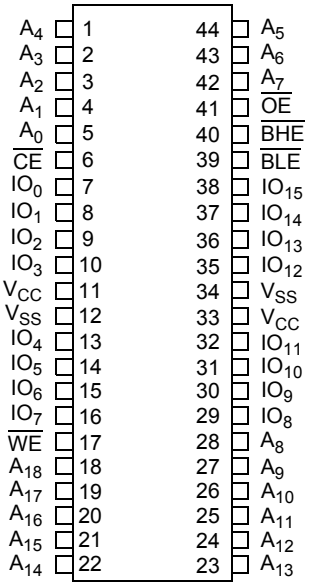
Product Portfolio

Product	Range	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating I_{CC}, (mA)				Standby, I_{SB2} (µA)	
						f = 1 MHz		f = f_{max}			
		Min	Typ[2]	Max		Typ[2]	Max	Typ[2]	Max	Typ[2]	Max
CY62157ELL	Industrial	4.5	5.0	5.5	45	1.8	3	18	25	2	8
CY62157ELL	Automotive	4.5	5.0	5.5	55	1.8	4	18	35	2	30

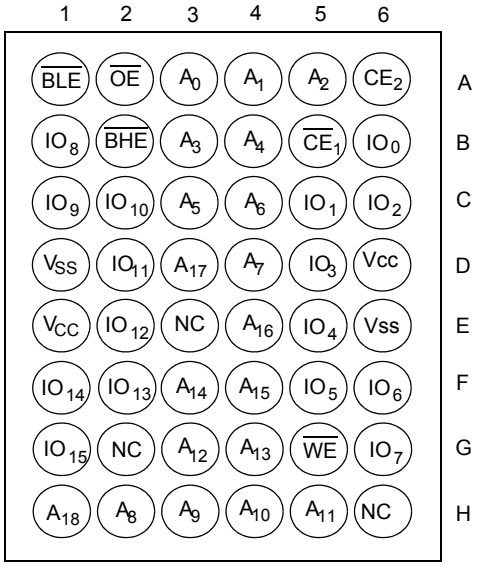
Pin Configuration

The following pictures show the TSOP II and VFBGA pinouts.[3, 4]

TSOP II
Top View



VFBGA
Top View



Notes
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25°C$.
3. NC pins are not connected on the die.
4. The 44-pin TSOP II package has only one chip enable ($\overline{CE}$) pin.

Maximum Ratings

Exceeding maximum ratings may shorten the battery life of the device. User guidelines are not tested.

Storage Temperature ..... –65°C to + 150°C

Ambient Temperature with Power Applied ..... –55°C to + 125°C

Supply Voltage to Ground Potential ..... –0.5V to 6.0V

DC Voltage Applied to Outputs in High-Z State[5, 6] ..... –0.5V to 6.0V

DC Input Voltage[5, 6] ..... –0.5V to 6.0V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V (MIL-STD-883, Method 3015)

Latch up Current ..... > 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}[7]
CY62157ELL	Industrial	–40°C to +85°C	4.5V to 5.5V
	Automotive	–40°C to +125°C	

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	45 ns (Industrial)			55 ns (Automotive)			Unit
			Min	Typ[2]	Max	Min	Typ[2]	Max	
V_{OH}	Output HIGH Voltage	I_{OH} = –1 mA	2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA			0.4			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC} = 4.5V to 5.5V	2.2		V_{CC} + 0.5	2.2		V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage	V_{CC} = 4.5V to 5.5V	–0.5		0.8	–0.5		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}	–1		+1	–4		+4	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled	–1		+1	–4		+4	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{max} = 1/t_{RC}; V_{CC} = $V_{CC(max)}$, I_{OUT} = 0 mA CMOS levels		18	25		18	35	mA
		f = 1 MHz; V_{CC} = $V_{CC(max)}$, I_{OUT} = 0 mA CMOS levels		1.8	3		1.8	4	
I_{SB1}	Automatic CE Power Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V, V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f = 0 (OE, BHE, BLE and WE), V_{CC} = $V_{CC(max)}$		2	8		2	30	µA
I_{SB2} [8]	Automatic CE Power Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = $V_{CC(max)}$		2	8		2	30	µA

Capacitance[9]

Parameter	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

Notes

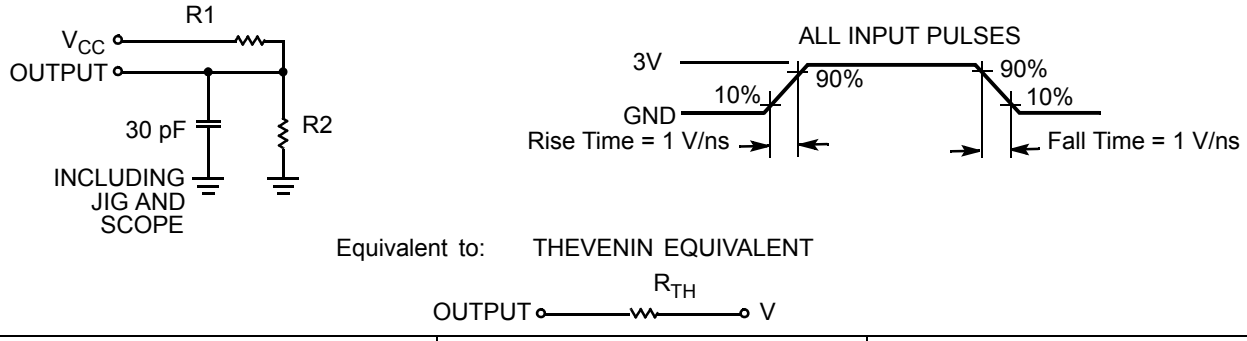
5. $V_{IL(min)}$ = –2.0V for pulse durations less than 20 ns for I < 30 mA.
6. $V_{IH(max)}$ = V_{CC} + 0.75V for pulse durations less than 20 ns.
7. Full device AC operation assumes a 100 µs ramp time from 0 to V_{CC}(min) and 200 µs wait time after V_{CC} stabilization.
8. Only chip enables ($\overline{CE}_1$ and CE_2) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
9. Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance [9]

Parameter	Description	Test Conditions	TSOP II	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	77	72	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		13	8.86	°C/W

AC Test Loads and Waveforms

Figure 1. AC Test Loads and Waveforms



Parameters	Values	Unit
R1	1800	Ω
R2	990	Ω
R_{TH}	639	Ω
V_{TH}	1.77	V

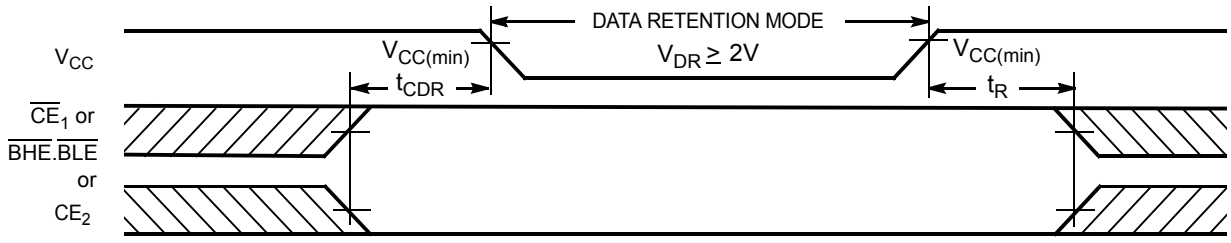
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions		Min	Typ [2]	Max	Unit
V_{DR}	V_{CC} for Data Retention			2			V
I_{CCDR} [8]	Data Retention Current	V_{CC}=2V, $\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	Industrial			8	µA
			Automotive			30	
t_{CDR} [9]	Chip Deselect to Data Retention Time			0			ns
t_R [10]	Operation Recovery Time			t_{RC}			ns

Data Retention Waveform[11]

Figure 2. Data Retention Waveform



Notes

10. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.
11. $\overline{BHE}.\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Deselect the chip by either disabling chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

Switching Characteristics

Over the Operating Range[12, 13]

Parameter	Description	45 ns (Industrial)		55 ns (Automotive)		Unit
		Min	Max	Min	Max	
Read Cycle						
t_{RC}	Read Cycle Time	45		55		ns
t_{AA}	Address to Data Valid		45		55	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Data Valid		45		55	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22		25	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW-Z[14]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[14, 15]		18		20	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Low-Z[14]	10		10		ns
t_{HZCE}	$\overline{CE}_1$ HIGH and CE_2 LOW to High-Z[14, 15]		18		20	ns
t_{PU}	$\overline{CE}_1$ LOW and CE_2 HIGH to Power Up	0		0		ns
t_{PD}	$\overline{CE}_1$ HIGH and CE_2 LOW to Power Down		45		55	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Data Valid		45		55	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Low-Z[14]	10		10		ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to HIGH-Z[14, 15]		18		20	ns
Write Cycle[16]						
t_{WC}	Write Cycle Time	45		55		ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Write End	35		40		ns
t_{AW}	Address Setup to Write End	35		40		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Setup to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		40		ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to Write End	35		40		ns
t_{SD}	Data Setup to Write End	25		25		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[14, 15]		18		20	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[14]	10		10		ns

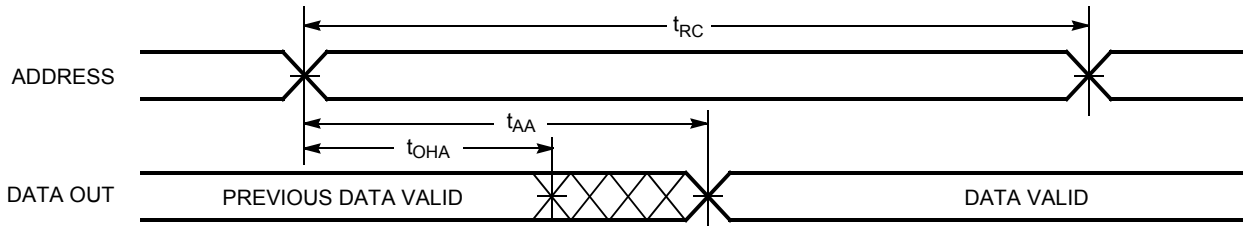
Notes

12. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" on page 4.
13. AC timing parameters are subject to byte enable signals ($\overline{BHE}$ or $\overline{BLE}$) not switching when chip is disabled. See application note AN13842 for further clarification.
14. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
15. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
16. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}_1 = V_{IL}$, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}, and $CE_2 = V_{IH}$. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.

Switching Waveforms

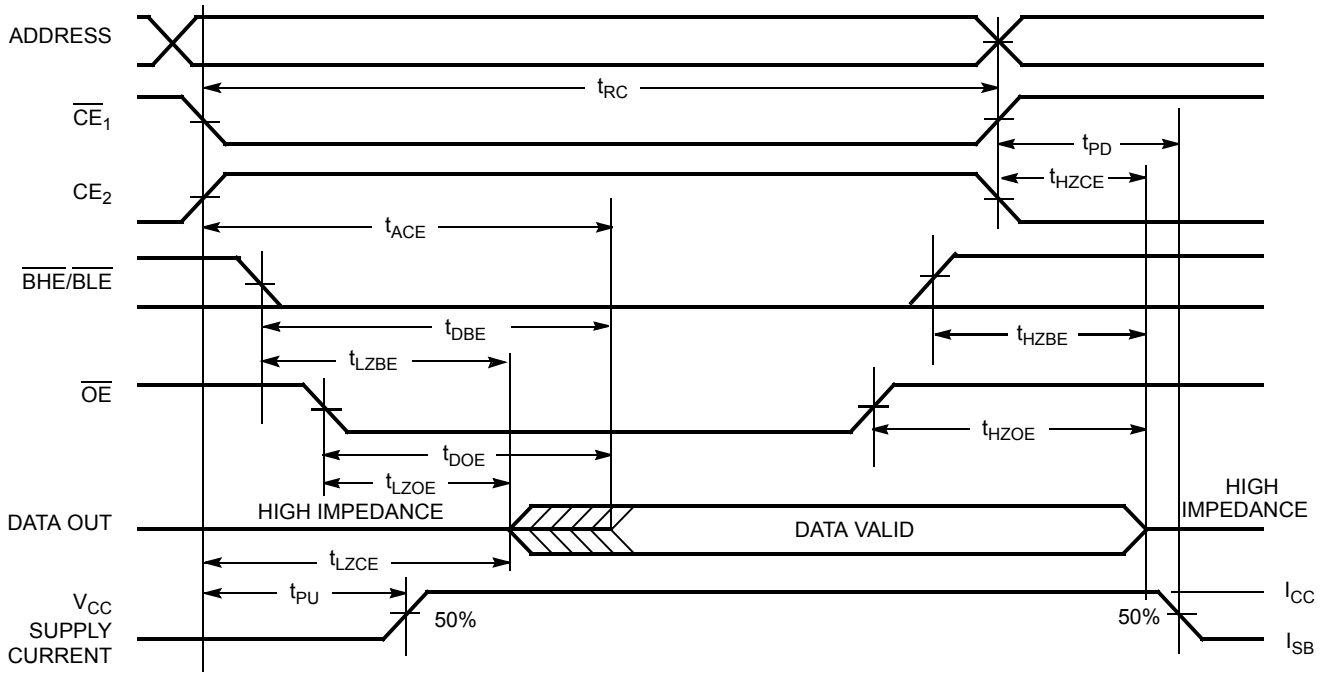
Read Cycle No. 1 (Address Transition Controlled)[17, 18]

Figure 3. Read Cycle No. 1



Read Cycle No. 2 ($\overline{OE}$ Controlled)[18, 19]

Figure 4. Read Cycle No. 2

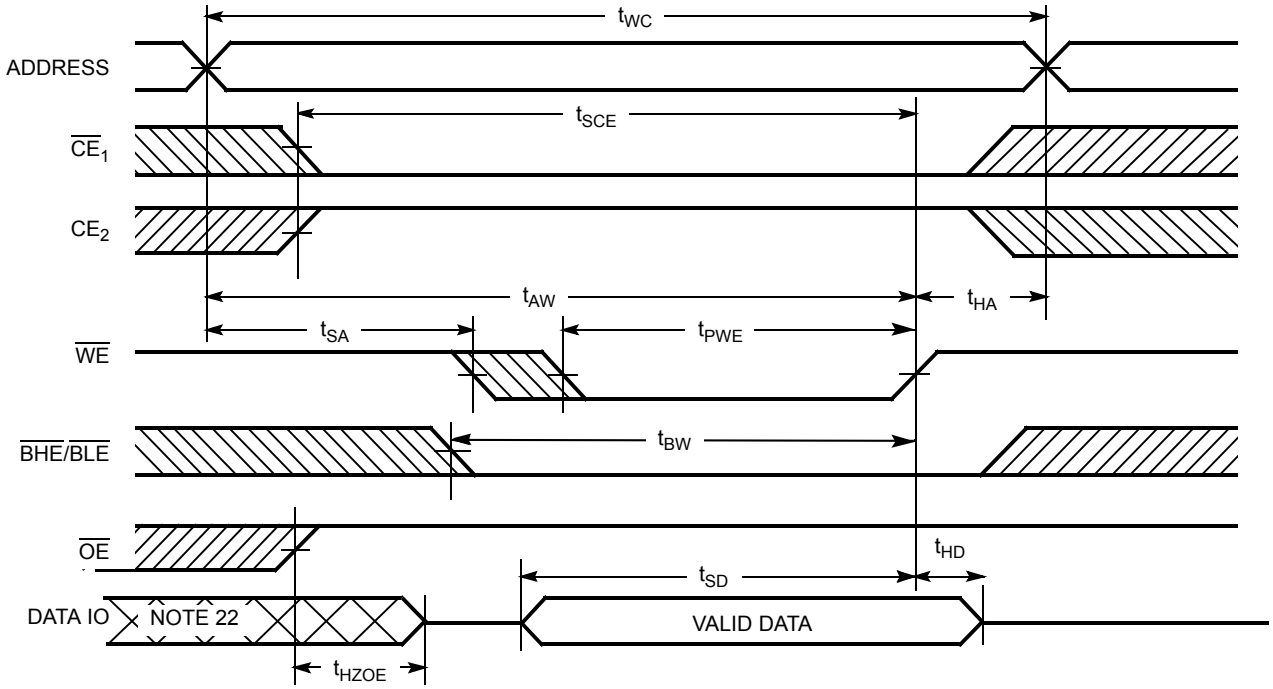


Notes
17. The device is continuously selected. $\overline{OE}$, $\overline{CE_1}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}.
18. $\overline{WE}$ is HIGH for read cycle.
19. Address valid before or similar to $\overline{CE_1}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW and CE_2 transition HIGH.

Switching Waveforms (continued)

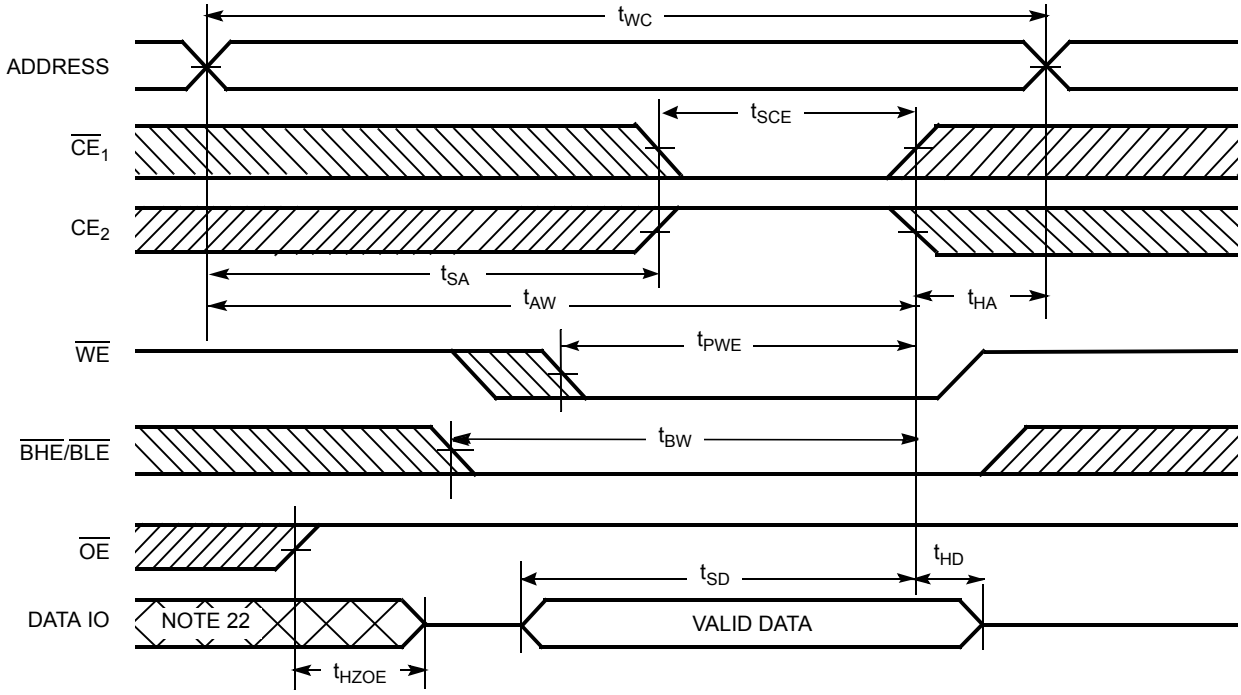
Write Cycle No. 1 ($\overline{WE}$ Controlled)[16, 20, 21]

Figure 5. Write Cycle No. 1



Write Cycle No. 2 ($\overline{CE_1}$ or CE_2 Controlled)[16, 20, 21]

Figure 6. Write Cycle No. 2



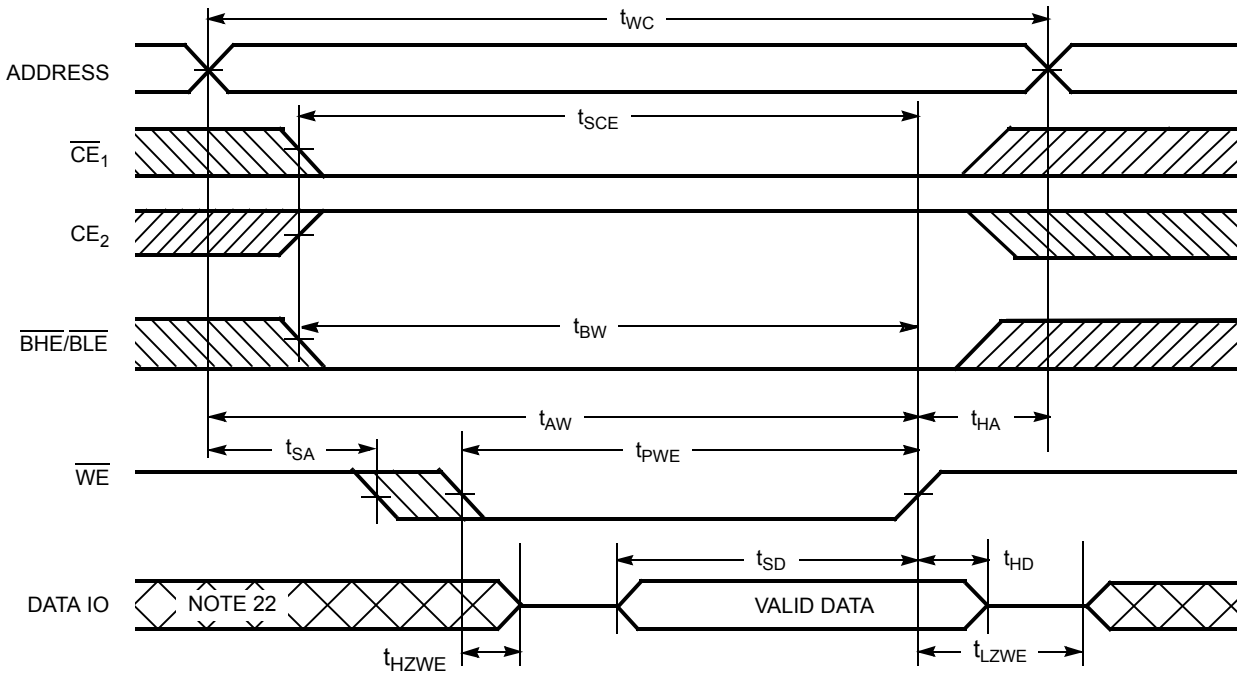
Notes

20. Data IO is high impedance if $\overline{OE} = V_{IH}$.
21. If $\overline{CE_1}$ goes HIGH and CE_2 goes LOW simultaneously with $\overline{WE} = V_{IH}$, the output remains in a high impedance state.
22. During this period, the IOs are in output state. Do not apply input signals.

Switching Waveforms (continued)

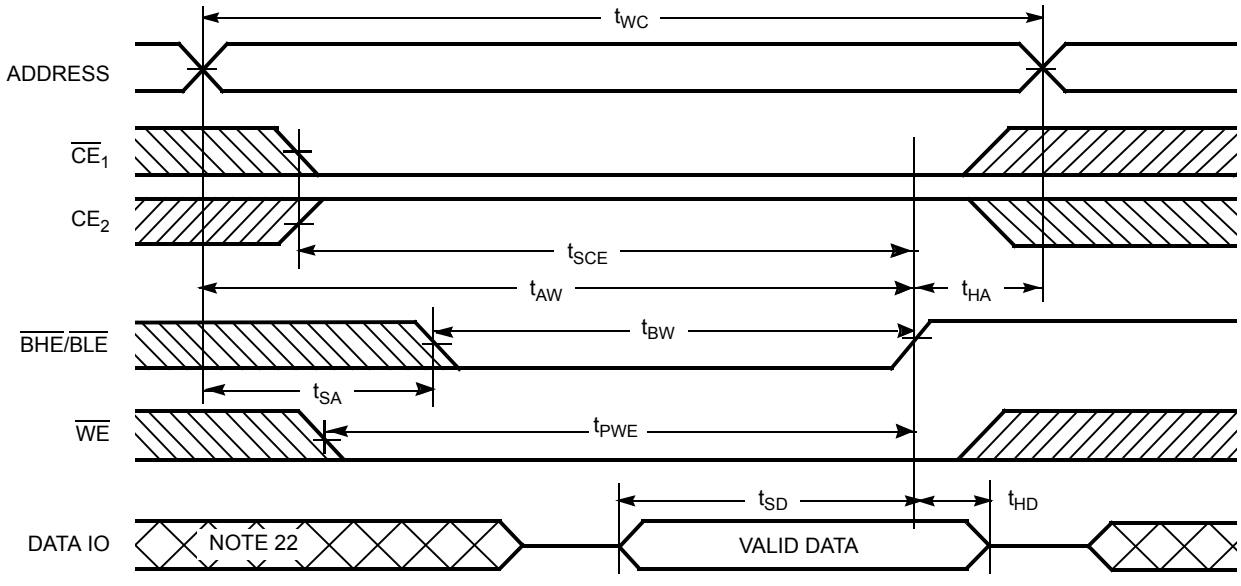
Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[21]

Figure 7. Write Cycle No. 3



Write Cycle No. 4 ($\overline{BHE}/\overline{BLE}$ Controlled, $\overline{OE}$ LOW)[21]

Figure 8. Write Cycle No. 4



Truth Table

$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High-Z	Deselect/Power Down	Standby (I_{SB})
X	L	X	X	X	X	High-Z	Deselect/Power Down	Standby (I_{SB})
X	X	X	X	H	H	High-Z	Deselect/Power Down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (IO_0–IO_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (IO_0–IO_7); High-Z (IO_8–IO_{15})	Read	Active (I_{CC})
L	H	H	L	L	H	High-Z (IO_0–IO_7); Data Out (IO_8–IO_{15})	Read	Active (I_{CC})
L	H	H	H	L	H	High-Z	Output Disabled	Active (I_{CC})
L	H	H	H	H	L	High-Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	L	High-Z	Output Disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (IO_0–IO_{15})	Write	Active (I_{CC})
L	H	L	X	H	L	Data In (IO_0–IO_7); High-Z (IO_8–IO_{15})	Write	Active (I_{CC})
L	H	L	X	L	H	High-Z (IO_0–IO_7); Data In (IO_8–IO_{15})	Write	Active (I_{CC})

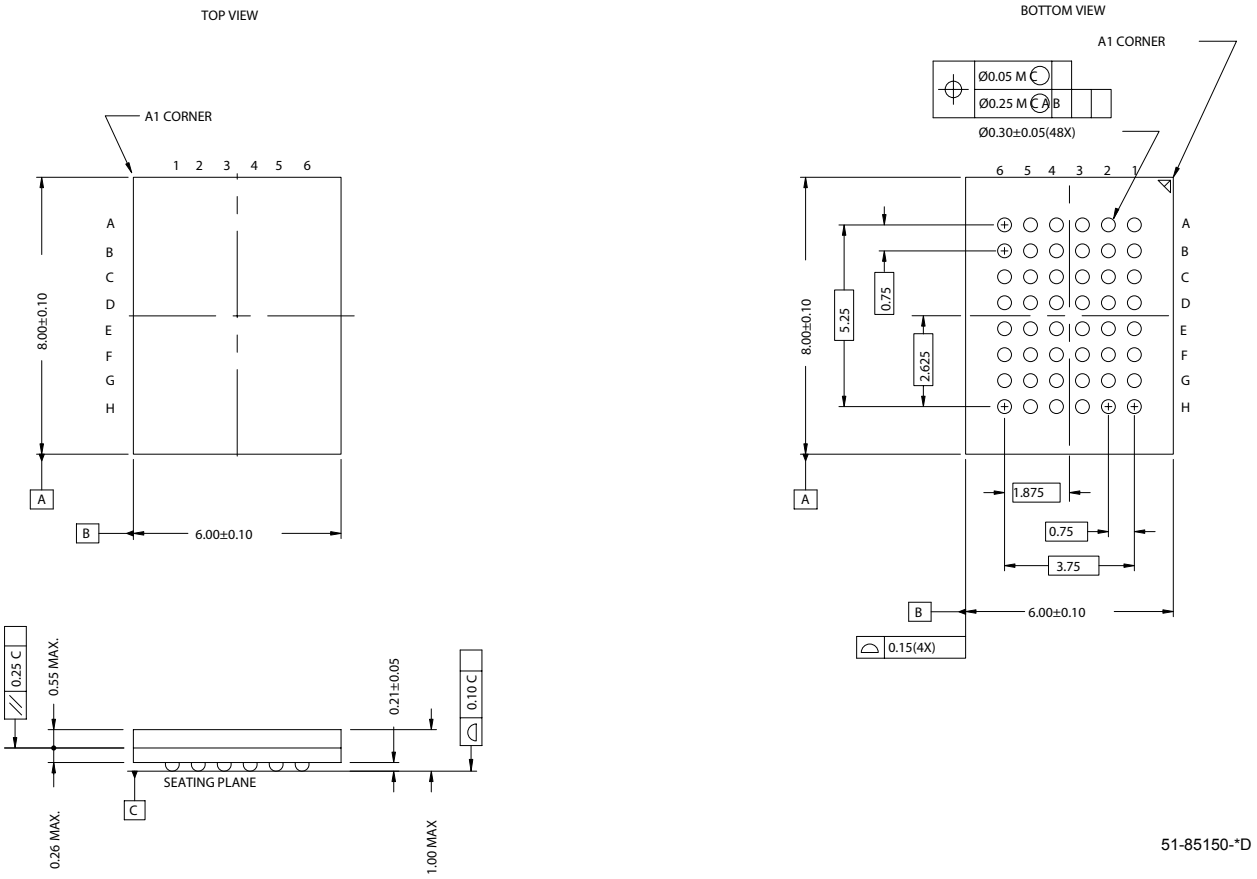
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62157ELL-45ZSXI	51-85087	44-pin Thin Small Outline Package Type II (Pb-free)	Industrial
55	CY62157ELL-55ZSXE	51-85087	44-pin Thin Small Outline Package Type II (Pb-free)	Automotive
	CY62157ELL-55BVXE	51-85150	48-ball Very Fine Pitch Ball Grid Array (Pb-free)	

Contact your local Cypress sales representative for availability of these parts.

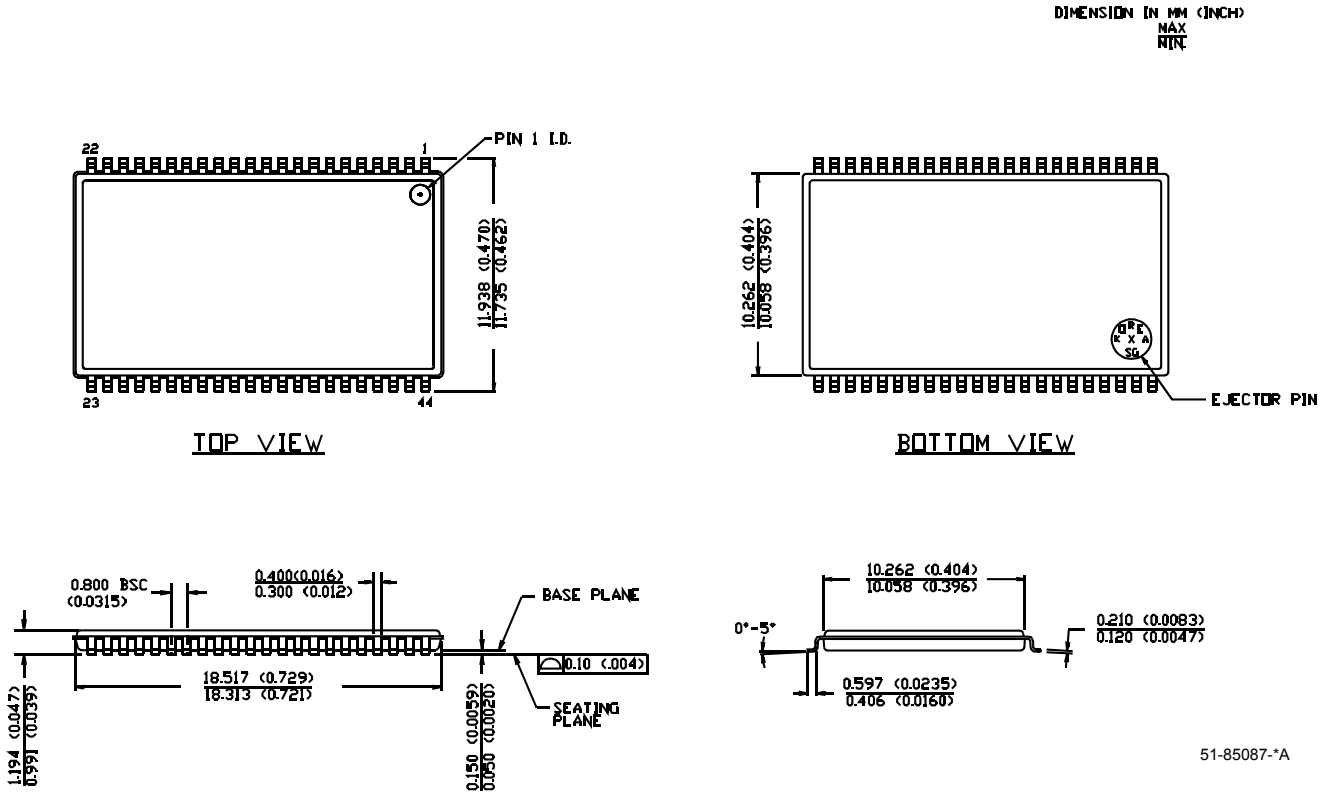
Package Diagrams

Figure 9. 48-Ball VFBGA (6 x 8 x 1 mm), 51-85150



Package Diagrams (continued)

Figure 10. 44-Pin TSOP II, 51-85087



Document History Page

Document Title: CY62157E MoBL®, 8-Mbit (512K x 16) Static RAM Document Number: 38-05695				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	291273	See ECN	PCI	New data sheet
*A	457689	See ECN	NXR	Added Automotive Product Removed Industrial Product Removed 35 ns and 45 ns speed bins Removed “L” bin Updated AC Test Loads table Corrected t_R in Data Retention Characteristics from 100 µs to t_{RC} ns Updated the Ordering Information and replaced the Package Name column with Package Diagram
*B	467033	See ECN	NXR	Added Industrial Product (Final Information) Removed 48 ball VFBGA package and its relevant information Changed the $I_{CC(typ)}$ value of Automotive from 2 mA to 1.8 mA for f = 1MHz Changed the $I_{SB2(typ)}$ value of Automotive from 5 µA to 1.8 µA Modified footnote #4 to include current limit Updated the Ordering Information table
*C	569114	See ECN	VKN	Added 48 ball VFBGA package Updated Logic Block Diagram Added footnote #3 Updated the Ordering Information table
*D	925501	See ECN	VKN	Added footnote #9 related to I_{SB2} and I_{CCDR} Added footnote #14 related AC timing parameters
*E	1045801	See ECN	VKN	Converted Automotive specs from preliminary to final